





100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	Max I _D T _A = +25°C	
100V	125mΩ @ V _{GS} = 10V	TO252	6.4A	
1000	150mΩ @ V _{GS} = 6V	(DPAK)	5.8A	

Features

- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

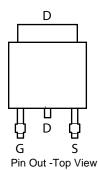
- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

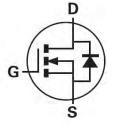
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)









Equivalent Circuit

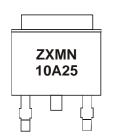
Ordering Information (4 & 5)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A25KTC	ZXMN10A25	13	16	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For Packaging Details, go to our website at http://www.diodes.com.
- 5. Products with Q-suffix are automotive grade. Automotive products are electrical and thermal the same as the commercial, except where specified.

Marking Information



ZXMN10A25 = Product Type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Ch	naracteristic		Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	100	V
Gate-Source voltage			V _{GS}	±20	V
		(Note 7)		6.4	
Continuous Drain current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	I _D	5	Α
		(Note 6)		4.2	
Pulsed Drain current (Note 8)		I _{DM}	21	A	
Continuous Source current (Body diode) (Note 7)			IS	10	A
Pulsed Source current (Body diode) (Note 8)			I _{SM}	21	A

Thermal Characteristics

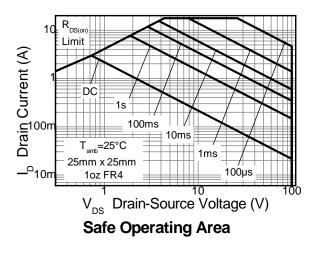
Characteristic	Symbol	Value	Unit	
	(Note 6)		4.25 34	
Power dissipation Linear derating factor	(Note 7)	P _D	9.85 78.7	W mW/°C
	(Note 9)		2.11 16.8	
	(Note 6)		29.4	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	12.7	2011
	(Note 9)		59.1	°C/W
Thermal Resistance, Junction to Lead (Note 10)		$R_{ heta JL}$	1.43	
Operating and storage temperature range	T _J , T _{STG}	-55 to 150	°C	

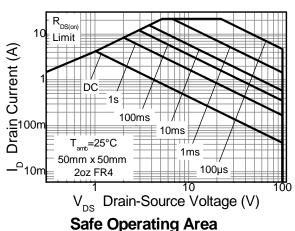
- 6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. For a device surface mounted on FR4 PCB measured at $t \le 10$ sec.
- 8. Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.

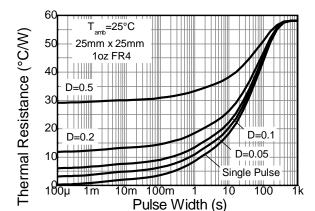
 9. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 10. Thermal resistance from junction to solder-point (at the end of the drain lead).

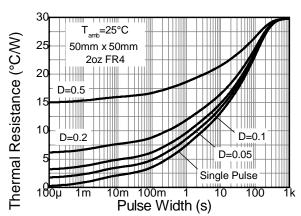


Thermal Characteristics



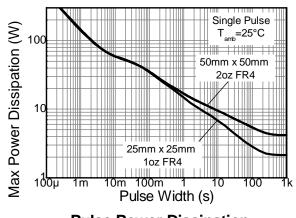


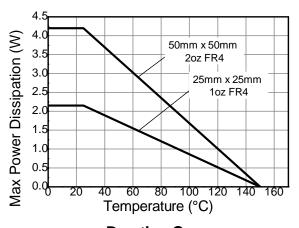




Transient Thermal Impedance

Transient Thermal Impedance





Pulse Power Dissipation

Derating Curve





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

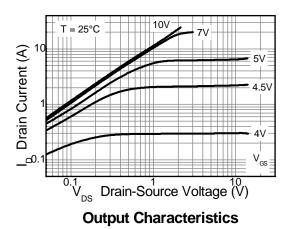
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	on
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	100			V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	2.0	_	4.0	V	$I_D = 250 \mu A, V_{DS} = V_{GS}$	
Static Drain Source On Decistores (Note 14)				125	0	$V_{GS} = 10V, I_D = 3.2A$	
Static Drain-Source On-Resistance (Note 11)	R _{DS (ON)}	_	_	150	mΩ	$V_{GS} = 6V, I_D = 2.6A$	
Forward Transconductance (Notes 11 & 12)	g fs	_	7.3	_	S	$V_{DS} = 15V, I_{D} = 2.9A$	
Diode Forward Voltage (Note 11)	V_{SD}	_	0.85	0.95	V	$I_S = 3.2A$, $V_{GS} = 0V$, $T_J = +25$ °C	
Reverse recovery time (Note 12)	t _{rr}		40.5	_	ns	$I_S = 2.9A$, di/dt = 100A/ μ s	
Reverse recovery charge (Note 12)	Qrr	_	62	_	nC	T _J = +25°C	
DYNAMIC CHARACTERISTICS (Note 12)							
Input Capacitance	Ciss	_	859	_	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	57.3	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	33	_	pF		
Total Gate Charge (Note 13)	Qq	_	9.6	_	nC	$V_{GS} = 5V$	
Total Gate Charge (Note 13)	Qq	_	17.16	_	nC	V _{DS} = 50V I _D = 2.9A	
Gate-Source Charge (Note 13)	Qgs	_	3.77	_	nC		
Gate-Drain Charge (Note 13)	Q_{gd}	_	5.36	_	nC		
Turn-On Delay Time (Note 13)	t _{D(on)}	_	4.9	_	ns	$V_{DD} = 50V, V_{GS} = 10V$ $I_D = 1A, R_G \cong 6.0\Omega$	
Turn-On Rise Time (Note 13)	tr	_	3.7	_	ns		
Turn-Off Delay Time (Note 13)	t _{D(off)}	_	17.7	_	ns		
Turn-Off Fall Time (Note 13)	t _f	_	9.4		ns		

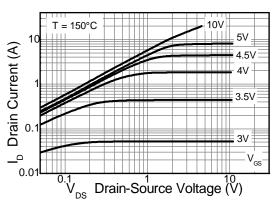
Notes:

- 11. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
 12. For design aid only, not subject to production testing.
 13. Switching characteristics are independent of operating junction temperatures.

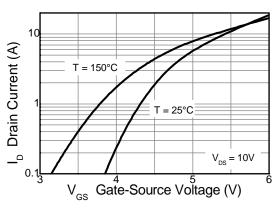


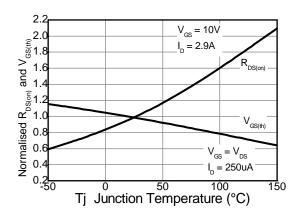
Typical Characteristics





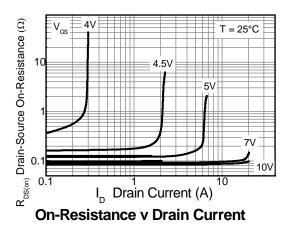
Output Characteristics

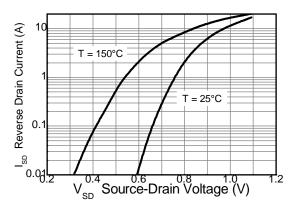




Typical Transfer Characteristics

Normalised Curves v Temperature

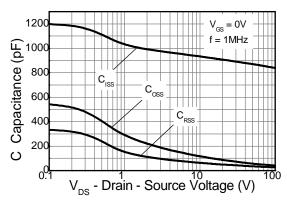




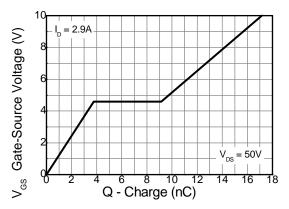
Source-Drain Diode Forward Voltage



Typical Characteristics (cont.)

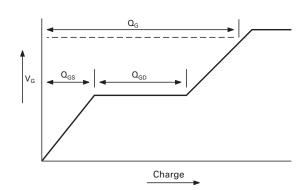


Capacitance v Drain-Source Voltage

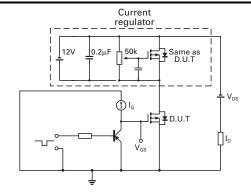


Gate-Source Voltage v Gate Charge

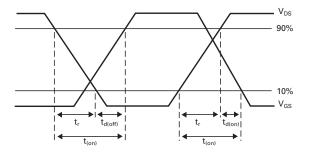
Test Circuits



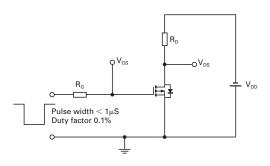
Basic gate charge waveform



Gate charge test circuit



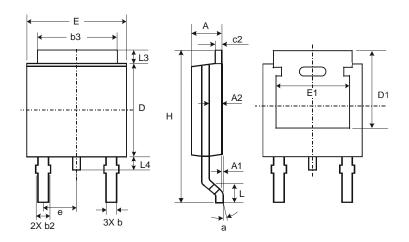
Switching time waveforms



Switching time test circuit

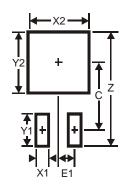


Package Outline Dimensions



TO252					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	1	1		
е	-	_	2.286		
Е	6.45	6.70	6.58		
E1	4.32	_	_		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	_		
All	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3





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